

an electrode pad covering a portion of said second electrode layer and leaving another portion of said second electrode layer uncovered; and

wherein said first electrode layer comprises a material which has an ionization potential lower than that of said second electrode layer, said second electrode layer comprises a material which has an ohmic characteristic to said semiconductor better than that of said first electrode layer, and the portion of said material of said second electrode layer which is uncovered by said electrode pad has been caused to be distributed more deeply into said surface layer than that of said first electrode layer by heat treatment in atmosphere comprising oxygen to provide a contact resistance between said electrode layer and said surface layer lower than said portion covered with said electrode pad, and a high contact resistance area that has been formed between said first electrode layer and said surface layer of said p-type semiconductor right under said pad, whereby electric current in downward direction is blocked at said high contact resistance area and flows to a lateral direction.

*See the attached Appendix for the changes made to effect the above claim(s).*